

Silicon PNP Power Transistors

2SA740

DESCRIPTION

- With TO-220 package
- Complement to type 2SC1448

APPLICATIONS

- Power amplifier applications
- Vertical output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

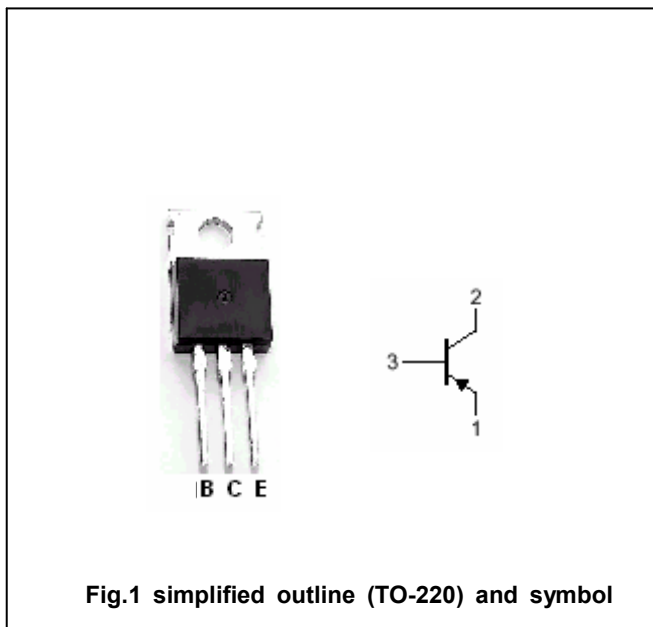


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-150	V
V _{CEO}	Collector-emitter voltage	Open base	-150	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1.5	A
I _E	Emitter current		1.5	A
P _C	Collector power dissipation	T _a =25°C	1.5	W
		T _C =25°C	25	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-1.5	V
V _{BE}	Base-emitter on voltage	I _C =-500mA; V _{CE} =-10V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-20	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-500mA; V _{CE} =-10V	40		140	
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		90		pF
f _T	Transition frequency	I _C =-500mA; V _{CE} =-10V		8		MHz

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PACKAGE OUTLINE

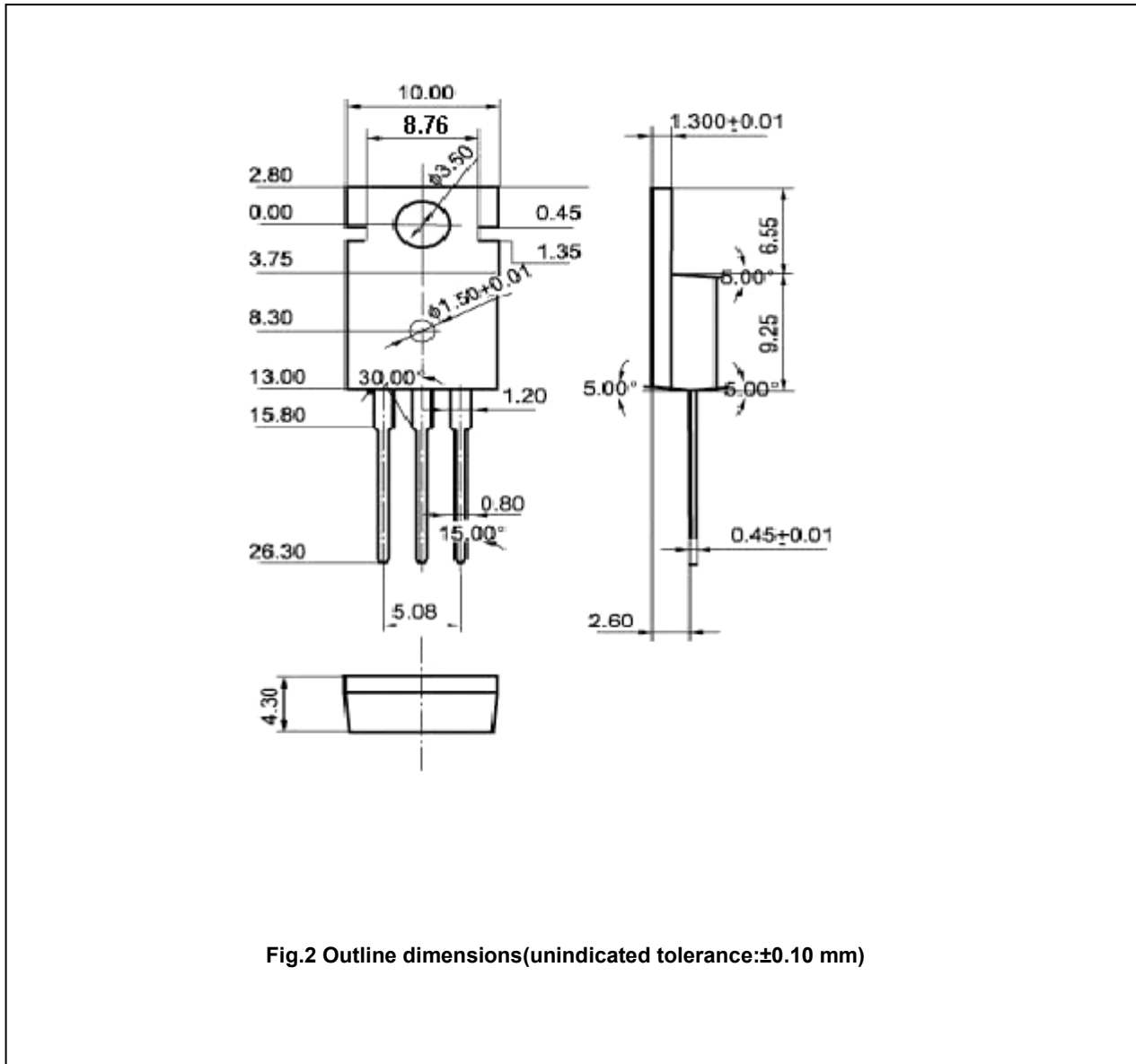


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)